BFP640ESD

Robust High Performance Low Noise Bipolar RF Transistor

Data Sheet

Revision 1.0, 2010-06-29

RF & Protection Devices

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (**www.infineon.com**).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

BFP640ESD, Robust High Performance Low Noise Bipolar RF Transistor

Revision History: 2010-06-29, Revision 1.0

Previous Revision:

Page	Subjects (major changes since last revision)

Trademarks of Infineon Technologies AG

BlueMoon™, COMNEON™, C166™, CROSSAVE™, CanPAK™, CIPOS™, CoolMOS™, CoolSET™, CORECONTROL™, DAVE™, EasyPIM™, EconoBRIDGE™, EconoDUAL™, EconoPACK™, EconoPIM™, EiceDRIVER™, EUPEC™, FCOS™, HITFET™, HybridPACK™, ISOFACE™, I²RF™, IsoPACK™, MIPAQ™, ModSTACK™, my-d™, NovalithIC™, OmniTune™, OptiMOS™, ORIGA™, PROFET™, PRO-SIL™, PRIMARION™, PrimePACK™, RASIC™, ReverSave™, SatRIC™, SensoNor™, SIEGET™, SINDRION™, SMARTi™, SmartLEWIS™, TEMPFET™, thinQ!™, TriCore™, TRENCHSTOP™, X-GOLD™, XMM™, X-PMU™, XPOSYS™.

Other Trademarks

Advance Design System™ (ADS) of Agilent Technologies, AMBA™, ARM™, MULTI-ICE™, PRIMECELL™, REALVIEW™, THUMB™ of ARM Limited, UK. AUTOSAR™ is licensed by AUTOSAR development partnership. Bluetooth™ of Bluetooth SIG Inc. CAT-iq™ of DECT Forum. COLOSSUS™, FirstGPS™ of Trimble Navigation Ltd. EMV™ of EMVCo, LLC (Visa Holdings Inc.). EPCOS™ of Epcos AG. FLEXGO™ of Microsoft Corporation. FlexRay™ is licensed by FlexRay Consortium. HYPERTERMINAL™ of Hilgraeve Incorporated. IEC™ of Commission Electrotechnique Internationale. IrDA™ of Infrared Data Association Corporation. ISO™ of INTERNATIONAL ORGANIZATION FOR STANDARDIZATION. MATLAB™ of MathWorks, Inc. MAXIM™ of Maxim Integrated Products, Inc. MICROTEC™, NUCLEUS™ of Mentor Graphics Corporation. Mifare™ of NXP. MIPI™ of MIPI Alliance, Inc. MIPS™ of MIPS Technologies, Inc., USA. muRata™ of MURATA MANUFACTURING CO., MICROWAVE OFFICE™ (MWO) of Applied Wave Research Inc., OmniVision™ of OmniVision Technologies, Inc. Openwave™ Openwave Systems Inc. RED HAT™ Red Hat, Inc. RFMD™ RF Micro Devices, Inc. SIRIUS™ of Sirius Sattelite Radio Inc. SOLARIS™ of Sun Microsystems, Inc. SPANSION™ of Spansion LLC Ltd. Symbian™ of Symbian Software Limited. TAIYO YUDEN™ of Taiyo Yuden Co. TEAKLITE™ of CEVA, Inc. TEKTRONIX™ of Tektronix Inc. TOKO™ of TOKO KABUSHIKI KAISHA TA. UNIX™ of X/Open Company Limited. VERILOG™, PALLADIUM™ of Cadence Design Systems, Inc. VLYNQ™ of Texas Instruments Incorporated. VXWORKS™, WIND RIVER™ of WIND RIVER SYSTEMS, INC. ZETEX™ of Diodes Zetex Limited.

Last Trademarks Update 2010-03-22

Table of Contents

List of Figures

List of Tables

Robust High Performance Low Noise Bipolar RF Transistor **BFP640ESD**

1 Features

- Robust high performance low noise amplifier based on Infineon´s reliable, high volume SiGe:C wafer technology
- 2 kV ESD robustness (HBM) due to integrated protection circuits
- High maximum RF input power of 21 dBm
- 0.65 dB minimum noise figure typical at 1.5 GHz, 0.7 dB at 2.4 GHz, 6 mA
- 26.5 dB maximum gain G_{ms} typical at 1.5 GHz, 23 dB at 2.4 GHz, 30 mA
- 27 dBm OIP_3 typical at 2.4 GHz, 30 mA
- Accurate SPICE GP model available to enable effective design in process (see chapter 6)
- Easy to use, Pb- and halogen free (RoHS compliant) standard package with visible leads

RoHS
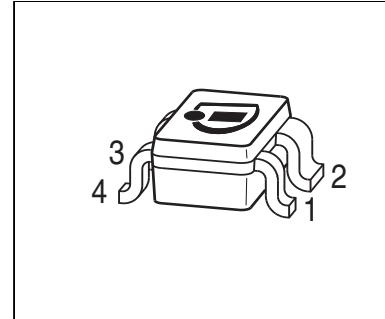
Applications

As Low Noise Amplifier (LNA) in

- Mobile, portable and fixed connectivity applications: WLAN 802.11a/b/g/n, WiMax 2.5 / 3.5 / 5GHz, UWB, Bluetooth
- Satellite communication systems: Navigation systems (GPS, Glonass), satellite radio (SDARs, DAB) and C-band LNB
- Multimedia applications such as mobile/portable TV, CATV, FM radio
- 3G/4G UMTS/LTE mobile phone applications
- ISM applications like RKE, AMR and Zigbee, as well as for emerging wireless applications.

As discrete active mixer, amplifier in VCOs and buffer amplifier

Attention: ESD (Electrostatic discharge) sensitive device, observe handling precautions

Product Name	Package	Pin Configuration				Marking
BFP640ESD	SOT343	1 = B	2 = E	3 = C	4 = E	T4s

Data Sheet   7   Revision 1.0, 2010-06-29

2 Product Brief

The BFP640ESD is a Silicon Germanium Carbon (SiGe:C) NPN Heterojunction wideband Bipolar RF Transistor (HBT) in a plastic dual emitter standard package with visible leads. The device is fitted with internal protection circuits, which enhance robustness against ESD and high RF input power strongly. The device combines robustness with very high RF gain and lowest noise figure at low operation current for use in a wide range of wireless applications.

The BFP640ESD is especially well-suited for portable battery-powered applications in which reduced power consumption is a key requirement. Device design supports collector voltages up to 4.1 V.

Table 1   Quick Reference DC Characteristics at T_A = 25°C

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Collector emitter breakdown voltage	$V_{(BR)CEO}$	4.1	4.7	–	V	I_C = 1 mA, I_B = 0
Collector base leakage current	I_{CBO}	–	–	500	nA	V_{CB} = 2 V, I_E = 0 Open emitter
DC current gain	h_{FE}	110	180	270		V_{CE} = 3 V, I_C = 30 mA
Collector current	I_C	–	–	50	mA	
Total power dissipation	P_{tot}	–	–	200	mW	$T_S \leq 88$ °C

Table 2   Quick Reference AC Characteristics at T_A = 25°C

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Transition frequency	f_T	–	46	–	GHz	V_{CE} = 3 V, I_C = 30 mA f = 1 GHz
V_{CE} = 3 V, f = 1.5 GHz						
Maximum power gain					dB	
Low noise operation point	G_{ms}	–	23.5	–		I_C = 6 mA
High linearity operation point	G_{ms}	–	26.5	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L = 50\ \Omega$
Low noise operation point	S_{21}	–	21	–		I_C = 6 mA
High linearity operation point	S_{21}	–	24	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	0.65	–		I_C = 6 mA
Associated gain	G_{ass}	–	23.5	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L = 50\ \Omega$
1 dB gain compression point	OP_{1dB}	–	12	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	26.5	–		I_C = 30 mA
V_{CE} = 3 V, f = 2.4 GHz						
Maximum power gain					dB	
Low noise operation point	G_{ms}	–	21	–		I_C = 6 mA
High linearity operation point	G_{ms}	–	23	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L = 50\ \Omega$
Low noise operation point	S_{21}	–	18	–		I_C = 6 mA
High linearity operation point	S_{21}	–	20	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	0.7	–		I_C = 6 mA
Associated gain	G_{ass}	–	20	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L = 50\ \Omega$
1 dB gain compression point	OP_{1dB}	–	12.5	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	27	–		I_C = 30 mA

3 Maximum Ratings

Table 3 **Maximum Ratings at T_A = 25°C (unless otherwise specified)**

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Collector emitter voltage	V_{CEO}				Open base
		–	4.1	V	T_A = 25 °C
		–	3.6	V	T_A = -55 °C
Collector base voltage[1]	V_{CBO}				Open emitter
		–	4.8	V	T_A = 25°C
		–	4.3	V	T_A = -55 °C
Collector emitter voltage[2]	V_{CES}				Emitter / base shortened
		–	4.1	V	T_A = 25°C
		–	3.6	V	T_A = -55 °C
Base current[3]	I_B	-10	6	mA	–
Collector current	I_C	–	50	mA	–
RF input power	P_{RFin}	–	21	dBm	–
ESD stress pulse[4]	V_{ESD}	-2	2	kV	HBM, all pins, acc. to JESD22-A114
Total power dissipation[5]	P_{tot}	–	200	mW	$T_S \leq 88$ °C
Junction temperature	T_J	–	150	°C	–
Storage temperature	T_{Stg}	-55	150	°C	–

1) Low V_{CBO} due to integrated protection circuits.
2) V_{CES} is identical to V_{CEO} due to integrated protection circuits.
3) Sustainable reverse bias current is high due to integrated protection circuits.
4) ESD robustness is high due to integrated protection circuits.
5) T_S is the soldering point temperature. T_S measured on the emitter lead at the soldering point of the pcb.

Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

4 Thermal Characteristics

Table 4 Thermal Resistance

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Junction - soldering point[1]	R_{thJS}	–	310	–	K/W	–

1)For calculation of R_{thJA} please refer to Application Note Thermal Resistance AN 077
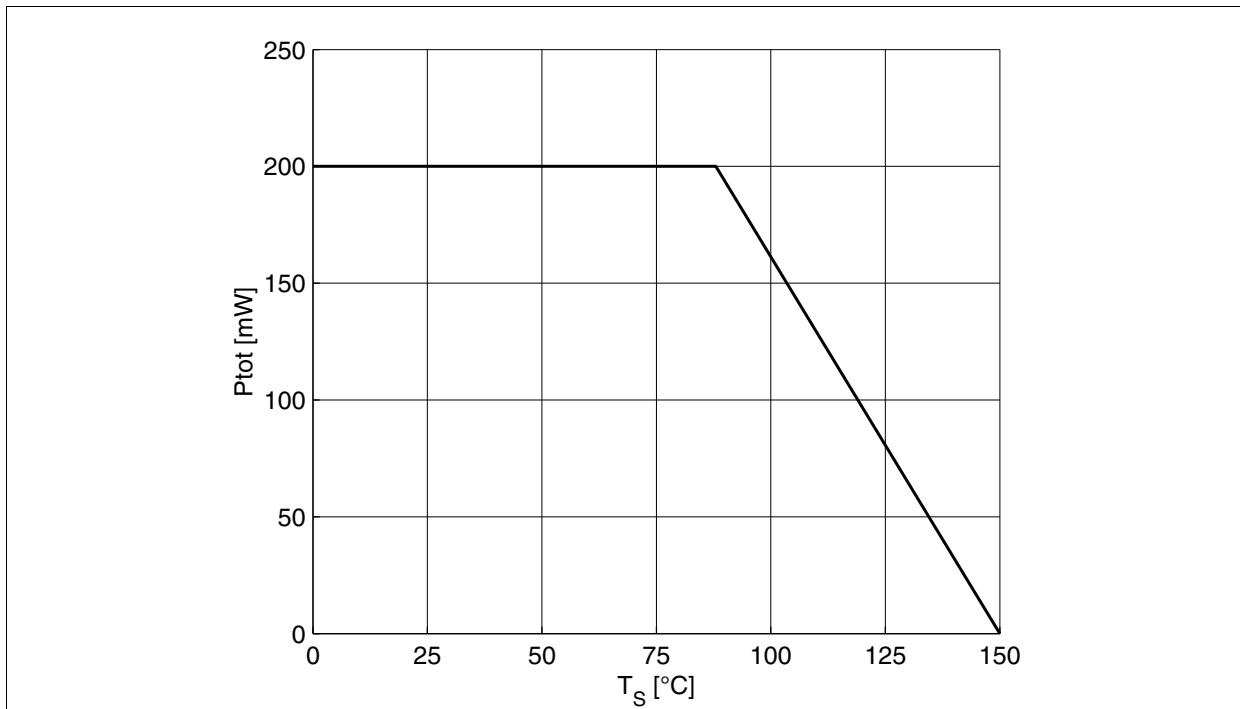

Figure 1 Total Power Dissipation $P_{tot} = f(T_s)$

5 Electrical Characteristics

5.1 DC Characteristics

Table 5 DC Characteristics at T_A = 25 °C

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	**Typ.**	**Max.**		
Collector emitter breakdown voltage	$V_{(BR)CEO}$	4.1	4.7	–	V	I_C = 1 mA, I_B = 0 Open base
Collector emitter leakage current	I_{CES}	–	–	500	nA	V_{CE} = 2 V, V_{BE} = 0 Emitter/base shortened
Collector base leakage current	I_{CBO}	–	–	500	nA	V_{CB} = 2 V, I_E = 0 Open emitter
Emitter base leakage current	I_{EBO}	–	–	10	μA	V_{EB} = 0.5 V, I_C = 0 Open collector
DC current gain	h_{FE}	110	180	270		V_{CE} = 3 V, I_C = 30 mA Pulse measured

5.2 General AC Characteristics

Table 6 General AC Characteristics at T_A = 25 °C

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	**Typ.**	**Max.**		
Transition frequency	f_T	–	46	–	GHz	V_{CE} = 3 V, I_C = 30 mA, f = 1 GHz
Collector base capacitance	C_{CB}	–	0.08	–	pF	V_{CB} = 3 V, V_{BE} = 0 V f = 1 MHz Emitter grounded
Collector emitter capacitance	C_{CE}	–	0.4	–	pF	V_{CE} = 3 V, V_{BE} = 0 V f = 1 MHz Base grounded
Emitter base capacitance	C_{EB}	–	0.7	–	pF	V_{EB} = 0.4 V, V_{CB} = 0 V f = 1 MHz Collector grounded

5.3 Frequency Dependent AC Characteristics

Measurement setup is a test fixture with Bias T's in a 50 Ω system, T_A = 25 °C
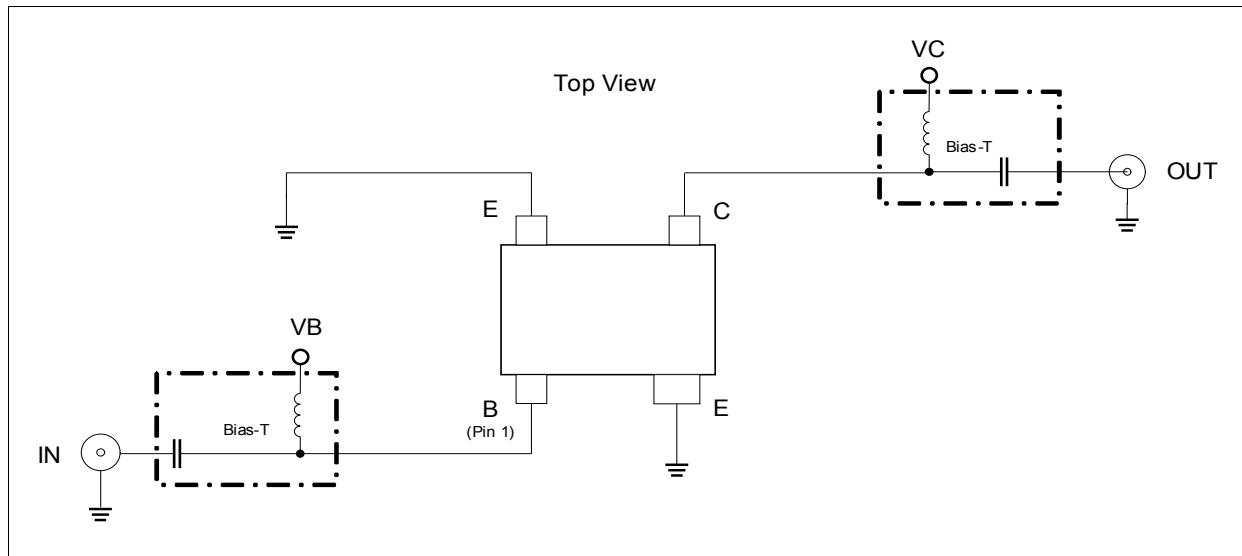
Figure 2   BFP640ESD Testing Circuit

Table 7   AC Characteristics, V_{CE} = 3 V, f = 150 MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	
Low noise operation point	G_{ms}	–	34	–		I_C = 6 mA
High linearity operation point	G_{ms}	–	39.5	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L$ = 50 Ω
Low noise operation point	S_{21}	–	25	–		I_C = 6 mA
High linearity operation point	S_{21}	–	35	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	0.6	–		I_C = 6 mA
Associated gain	G_{ass}	–	30	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L$ = 50 Ω
1 dB gain compression point	OP_{1dB}	–	11	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	25	–		I_C = 30 mA

Table 8   AC Characteristics, V_{CE} = 3 V, f = 450 MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	
Low noise operation point	G_{ms}	–	29	–		I_C = 6 mA
High linearity operation point	G_{ms}	–	34.5	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L$ = 50 Ω
Low noise operation point	S_{21}	–	24.5	–		I_C = 6 mA
High linearity operation point	S_{21}	–	32	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	0.6	–		I_C = 6 mA
Associated gain	G_{ass}	–	28.5	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L$ = 50 Ω
1 dB gain compression point	OP_{1dB}	–	11	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	25	–		I_C = 30 mA

Table 9   AC Characteristics, V_{CE} = 3 V, f = 900 MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	
Low noise operation point	G_{ms}	–	26	–		I_C = 6 mA
High linearity operation point	G_{ms}	–	30.5	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L$ = 50 Ω
Low noise operation point	S_{21}	–	23.5	–		I_C = 6 mA
High linearity operation point	S_{21}	–	28	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	0.6	–		I_C = 6 mA
Associated gain	G_{ass}	–	26	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L$ = 50 Ω
1 dB gain compression point	OP_{1dB}	–	11.5	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	26	–		I_C = 30 mA

Table 10   AC Characteristics, V_{CE} = 3 V, f = 1.5 GHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	
Low noise operation point	G_{ms}	–	23.5	–		I_C = 6 mA
High linearity operation point	G_{ms}	–	26.5	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L$ = 50 Ω
Low noise operation point	S_{21}	–	21	–		I_C = 6 mA
High linearity operation point	S_{21}	–	24	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	0.65	–		I_C = 6 mA
Associated gain	G_{ass}	–	23.5	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L$ = 50 Ω
1 dB gain compression point	OP_{1dB}	–	12	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	26.5	–		I_C = 30 mA

Table 11   AC Characteristics, V_{CE} = 3 V, f = 1.9 GHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	
Low noise operation point	G_{ms}	–	22.5	–		I_C = 6 mA
High linearity operation point	G_{ms}	–	25	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L$ = 50 Ω
Low noise operation point	S_{21}	–	19.5	–		I_C = 6 mA
High linearity operation point	S_{21}	–	22	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	0.65	–		I_C = 6 mA
Associated gain	G_{ass}	–	22	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L$ = 50 Ω
1 dB gain compression point	OP_{1dB}	–	12	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	27	–		I_C = 30 mA

Table 12   AC Characteristics, V_{CE} = 3 V, f = 2.4 GHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	
Low noise operation point	G_{ms}	–	21	–		I_C = 6 mA
High linearity operation point	G_{ms}	–	23	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L$ = 50 Ω
Low noise operation point	S_{21}	–	18	–		I_C = 6 mA
High linearity operation point	S_{21}	–	20	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	0.7	–		I_C = 6 mA
Associated gain	G_{ass}	–	20	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L$ = 50 Ω
1 dB gain compression point	OP_{1dB}	–	12.5	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	27	–		I_C = 30 mA

Table 13   AC Characteristics, V_{CE} = 3 V, f = 3.5 GHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	
Low noise operation point	G_{ma}	–	19	–		I_C = 6 mA
High linearity operation point	G_{ms}	–	19	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L$ = 50 Ω
Low noise operation point	S_{21}	–	15	–		I_C = 6 mA
High linearity operation point	S_{21}	–	17	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	0.8	–		I_C = 6 mA
Associated gain	G_{ass}	–	16	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L$ = 50 Ω
1 dB gain compression point	OP_{1dB}	–	12.5	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	26.5	–		I_C = 30 mA

Table 14   AC Characteristics, V_{CE} = 3 V, f = 5.5 GHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	
Low noise operation point	G_{ma}	–	14	–		I_C = 6 mA
High linearity operation point	G_{ma}	–	14.5	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L$ = 50 Ω
Low noise operation point	S_{21}	–	11	–		I_C = 6 mA
High linearity operation point	S_{21}	–	12.5	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	1.05	–		I_C = 6 mA
Associated gain	G_{ass}	–	11.5	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L$ = 50 Ω
1 dB gain compression point	OP_{1dB}	–	12.5	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	26	–		I_C = 30 mA

Table 15   AC Characteristics, V_{CE} = 3 V, f = 10 GHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	
Low noise operation point	G_{ms}	–	10	–		I_C = 6 mA
High linearity operation point	G_{ms}	–	10.5	–		I_C = 30 mA
Transducer gain					dB	$Z_S = Z_L$ = 50 Ω
Low noise operation point	S_{21}	–	4.5	–		I_C = 6 mA
High linearity operation point	S_{21}	–	6	–		I_C = 30 mA
Minimum noise figure					dB	$Z_S = Z_{opt}$
Minimum noise figure	NF_{min}	–	2	–		I_C = 6 mA
Associated gain	G_{ass}	–	7	–		I_C = 6 mA
Linearity					dBm	$Z_S = Z_L$ = 50 Ω
1 dB gain compression point	OP_{1dB}	–	11	–		I_C = 30 mA
3rd order intercept point	OIP_3	–	25.5	–		I_C = 30 mA

Note:

1. $G_{ms} = |S_{21} / S_{12}|$ for k < 1; $G_{ma} = |S_{21} / S_{12}|(k-(k^2-1)^{1/2})$ for k > 1
2. *In order to get the NF_{min} values stated in this chapter the test fixture losses have been subtracted from all measured result*
3. $OIP3_3$ *value depends on termination of all intermodulation frequency components. Termination used for this measurement is 50 Ω from 0.2 MHz to 12 GHz.*

5.4   Characteristic DC Diagrams
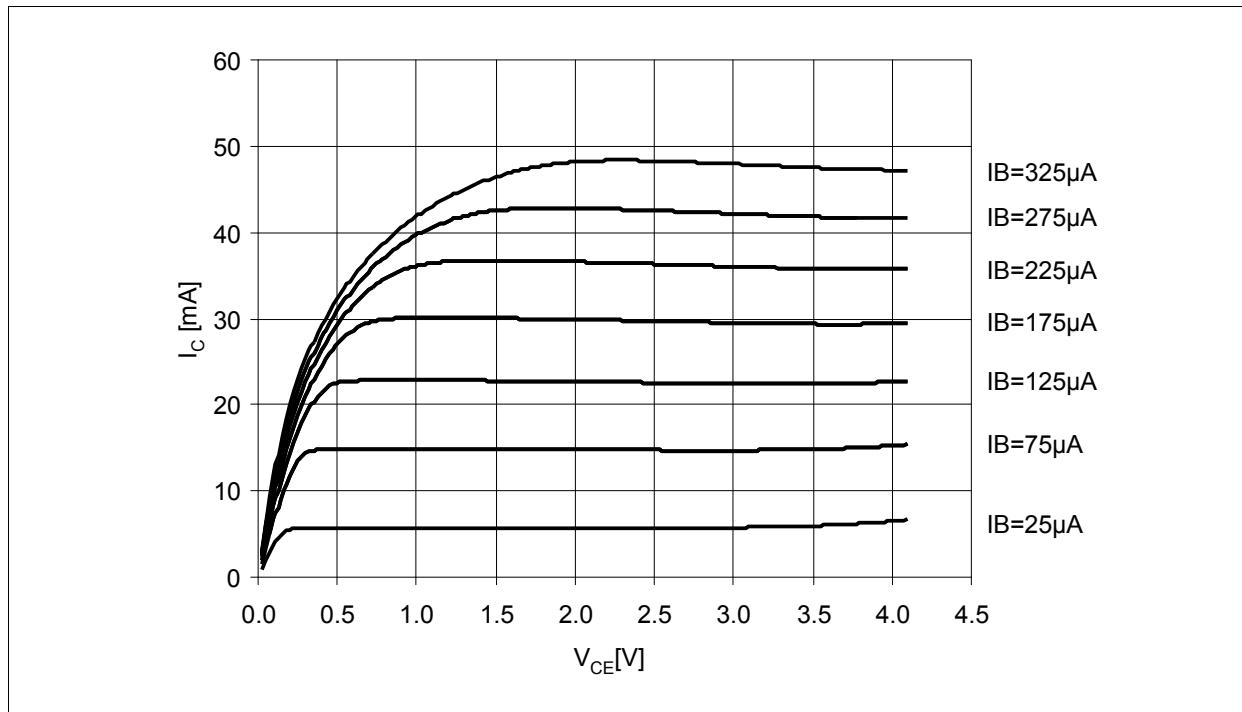
Figure 3   Collector Current vs. Collector Emitter Voltage $I_C = f(V_{CE})$, I_B **= Parameter**
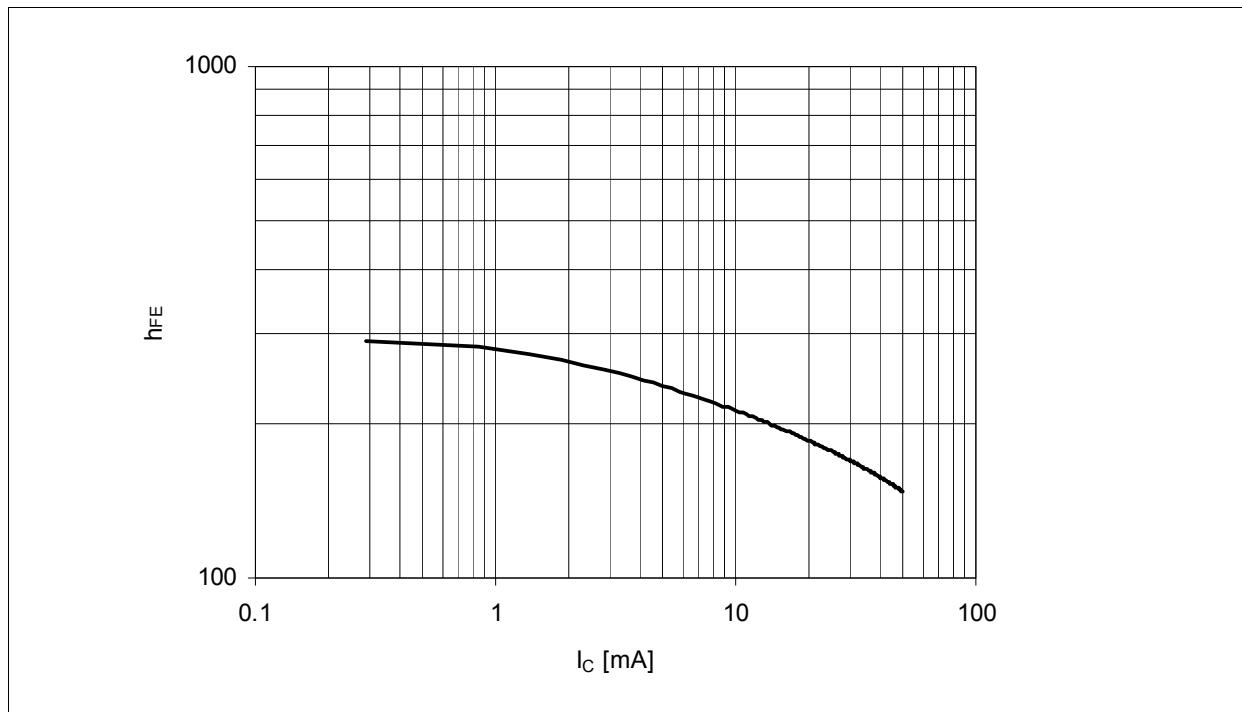

**Figure 4   DC Current Gain** $h_{FE} = f(I_C)$, V_{CE} **= 3 V**
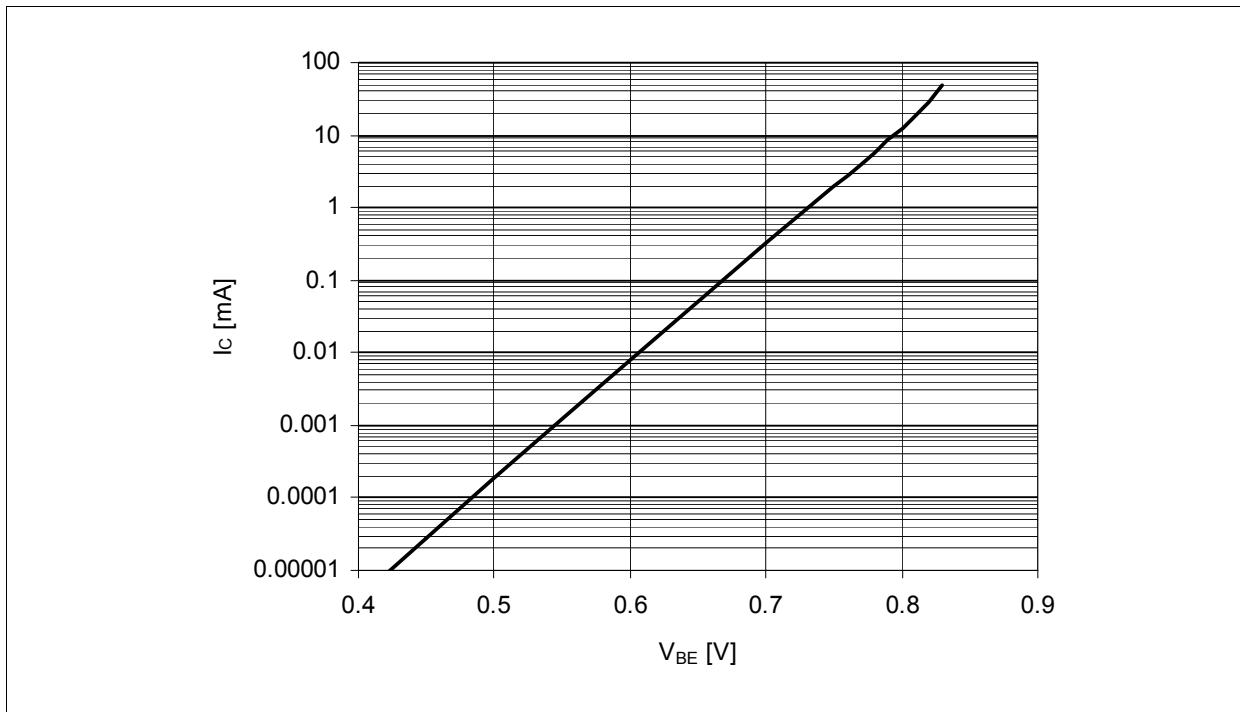
**Figure 5** Collector Current vs. Base Emitter Voltage $I_C = f(V_{BE})$, V_{CE} = 2 V
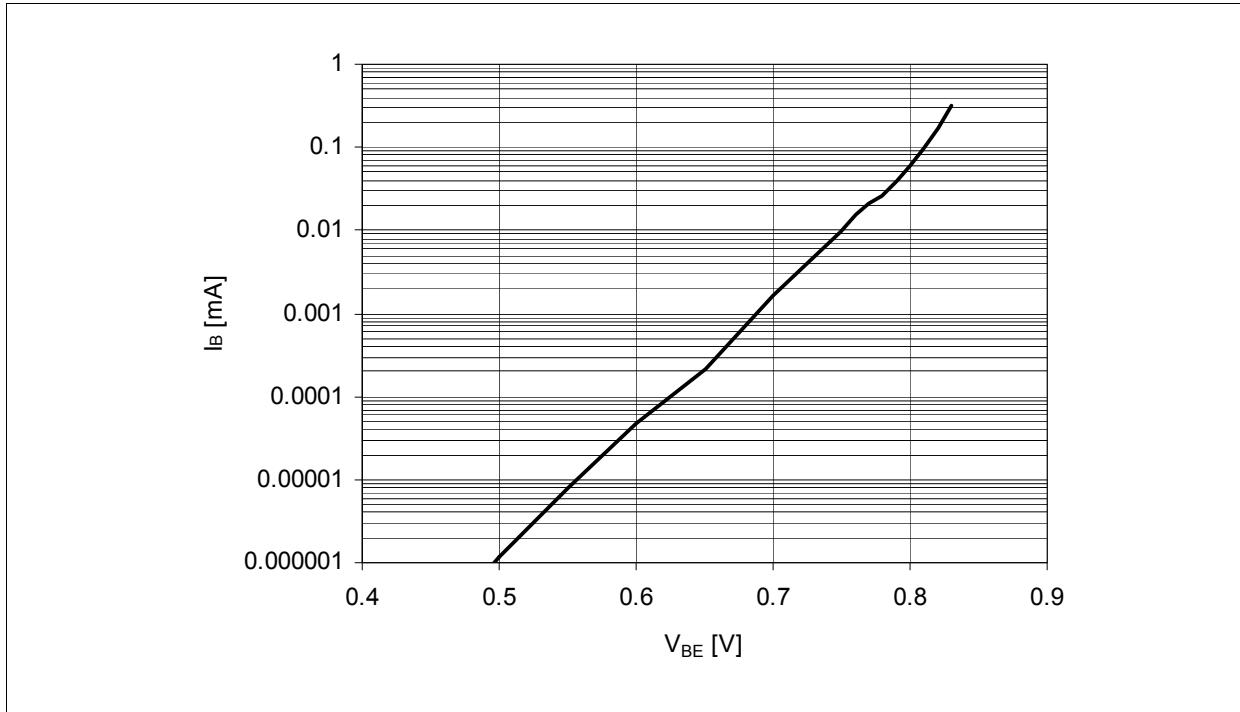
**Figure 6** Base Current vs. Base Emitter Forward Voltage $I_B = f(V_{BE})$, V_{CE} = 2 V
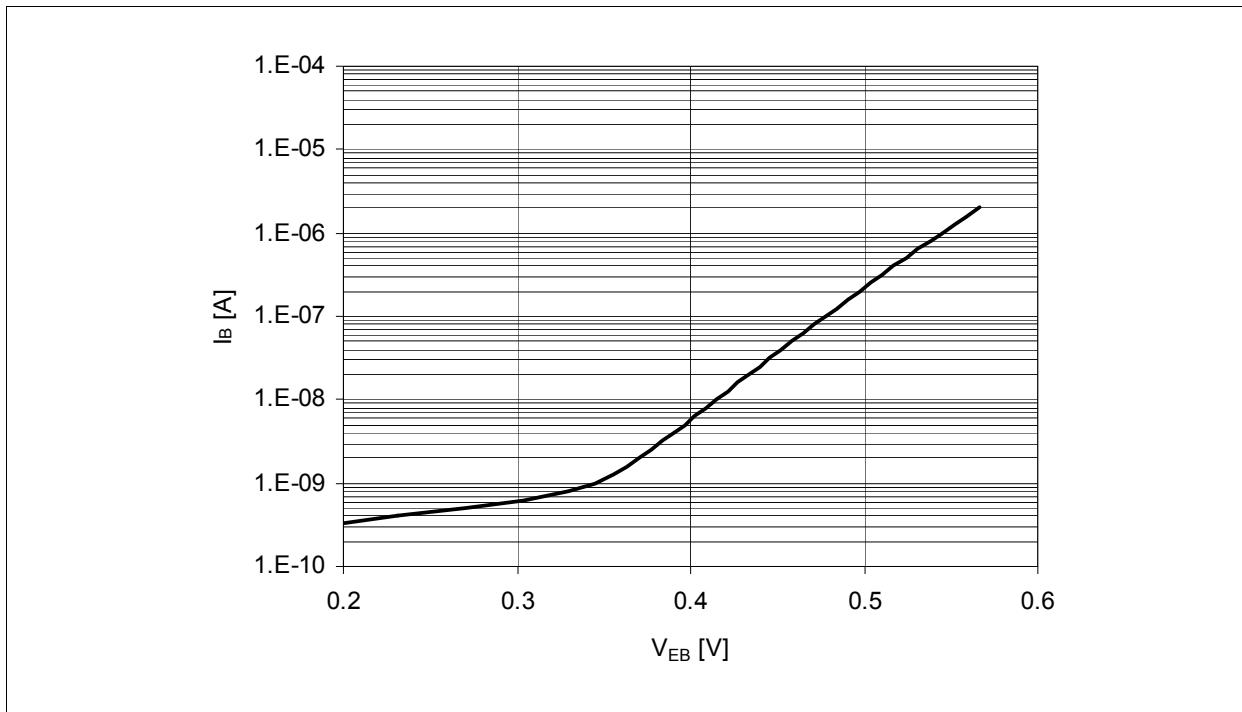
Figure 7   **Base Current vs. Base Emitter Reverse Voltage** $I_B = f(V_{EB})$, V_{CE} **= 2 V**

5.5 Characteristic AC Diagrams
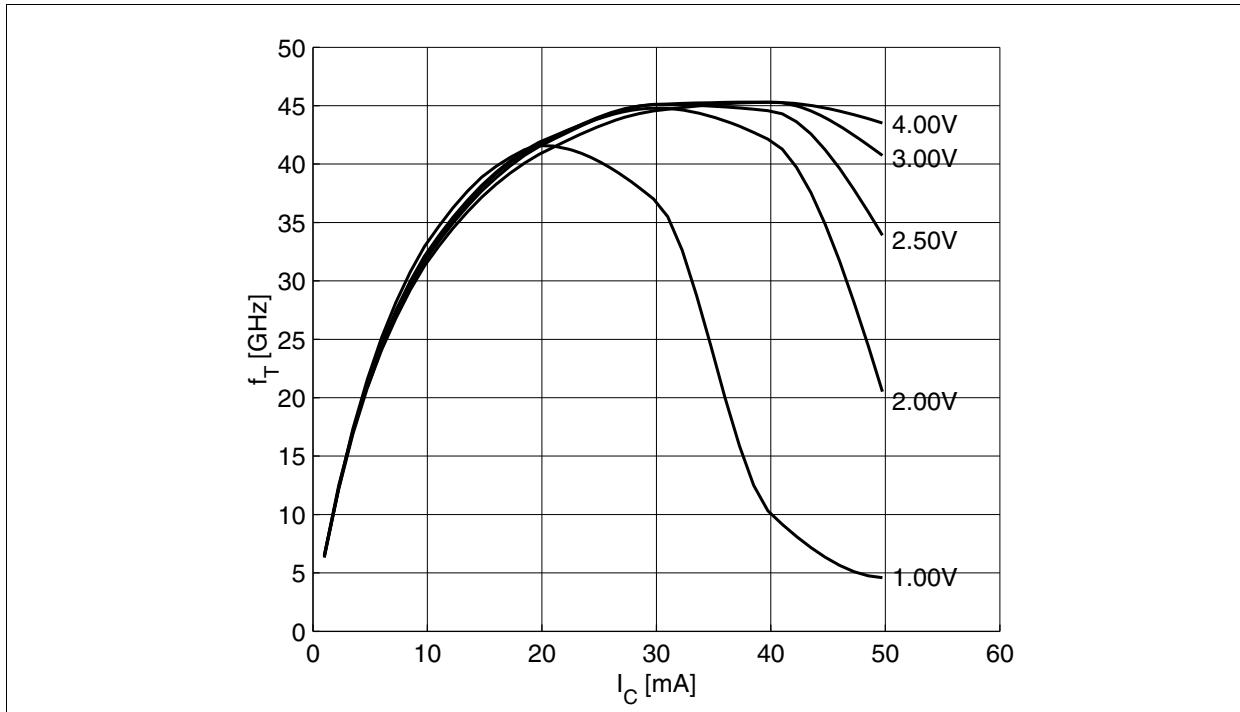
Figure 8 Transition Frequency $f_T = f(I_C)$, f = 1 GHz, V_{CE} = Parameter
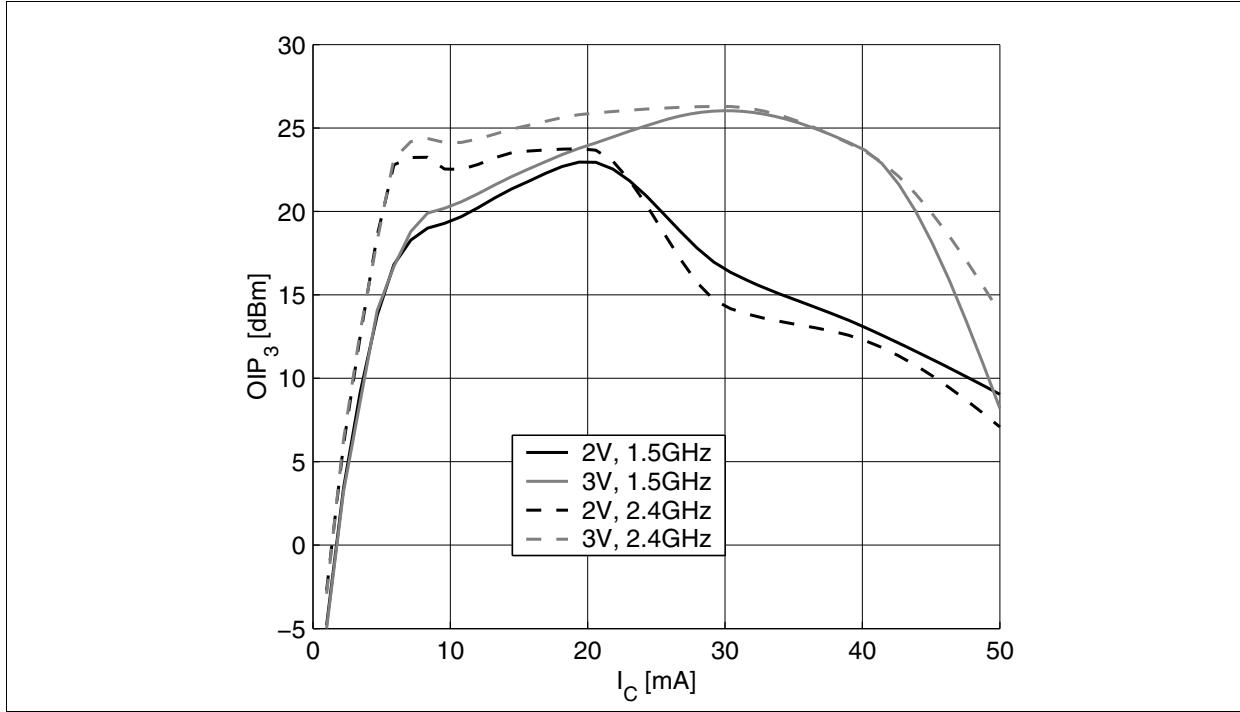
Figure 9 3rd Order Intercept Point $OIP_3 = f(I_C)$, $Z_S = Z_L$ = 50 Ω, V_{CE}, f = Parameters
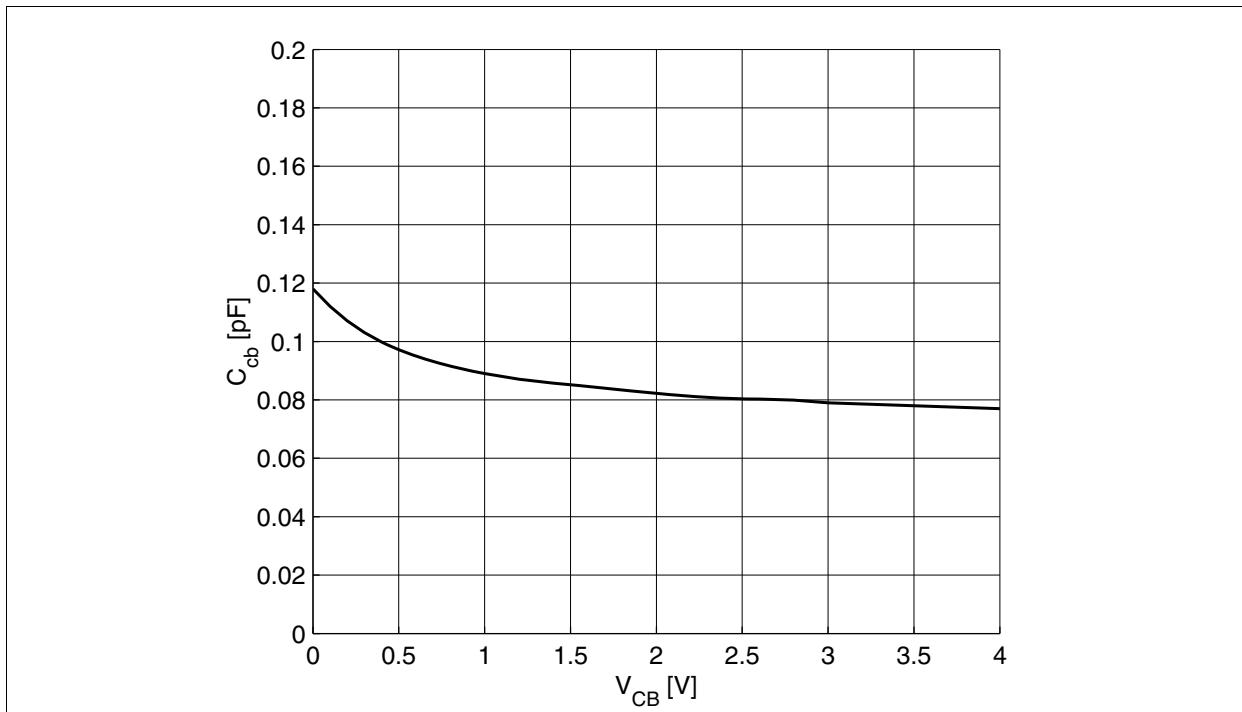
Figure 10   Collector Base Capacitance $C_{CB} = f(V_{CB})$, f = 1 MHz
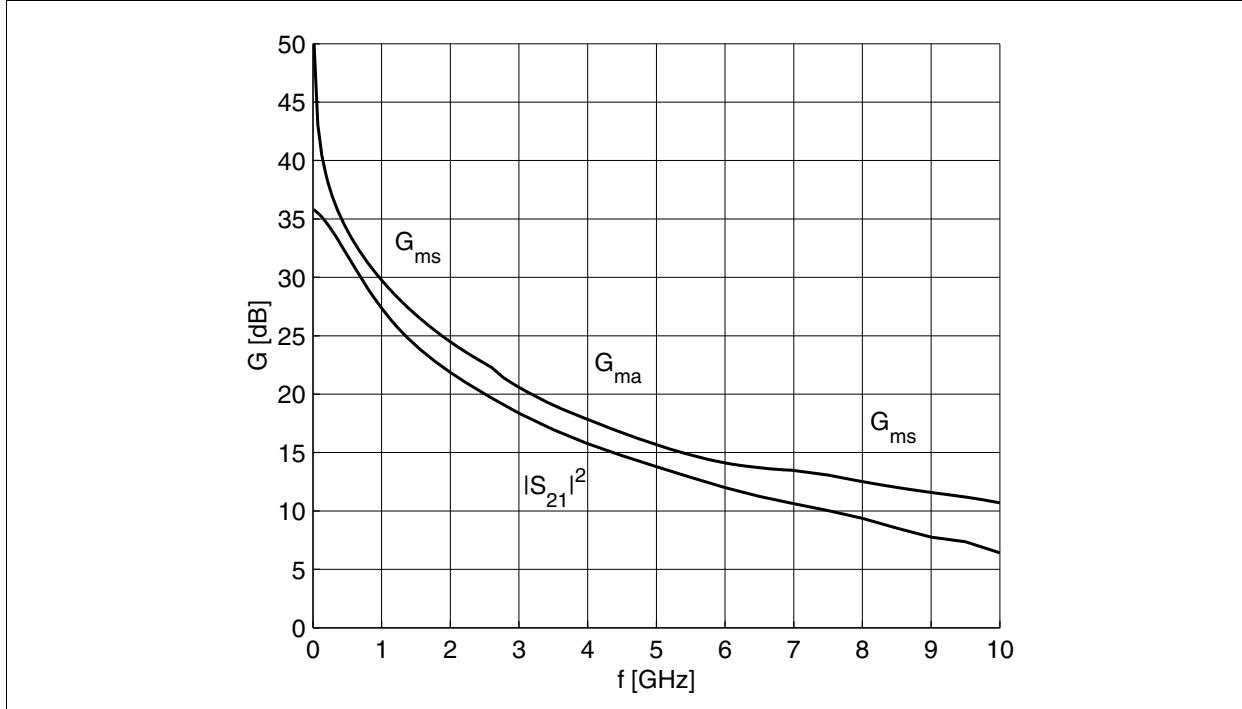
Figure 11   Gain G_{ma}, G_{ms}, $|S_{21}|^2 = f(f)$, V_{CE} = 3 V, I_C = 30 mA
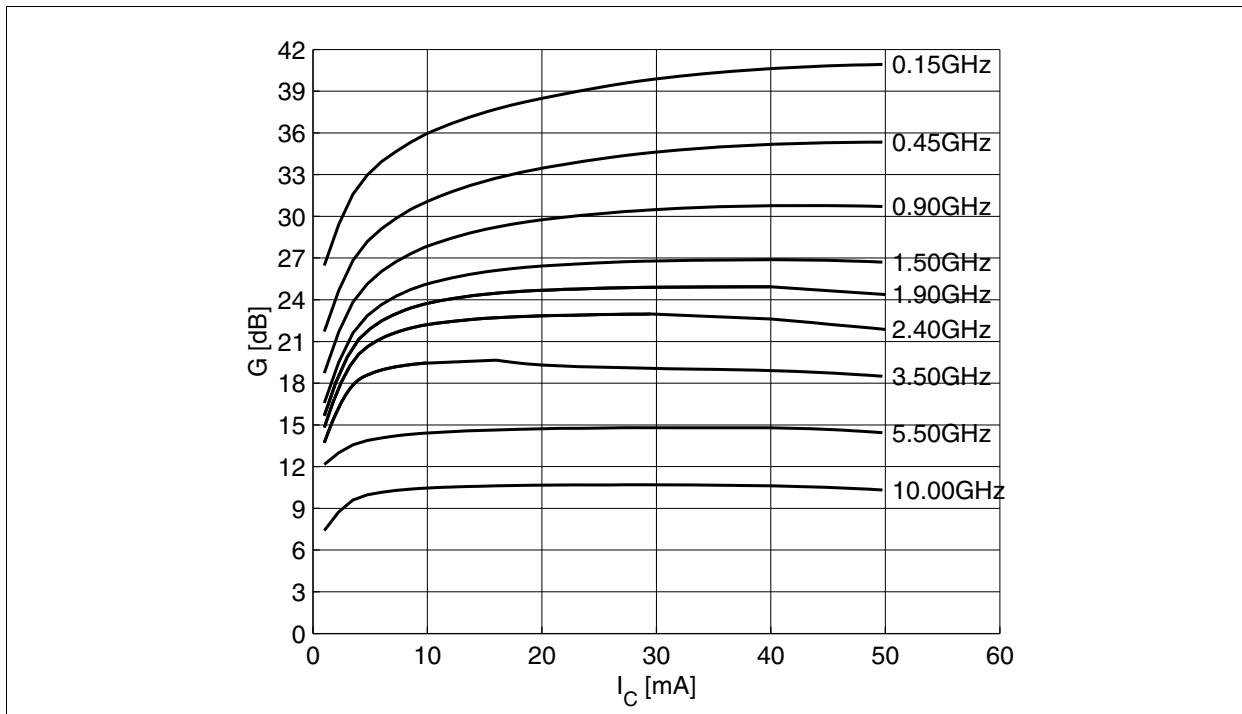
Figure 12   Maximum Power Gain $G_{max} = f(I_C)$, V_{CE} = 3 V, f = Parameter in GHz
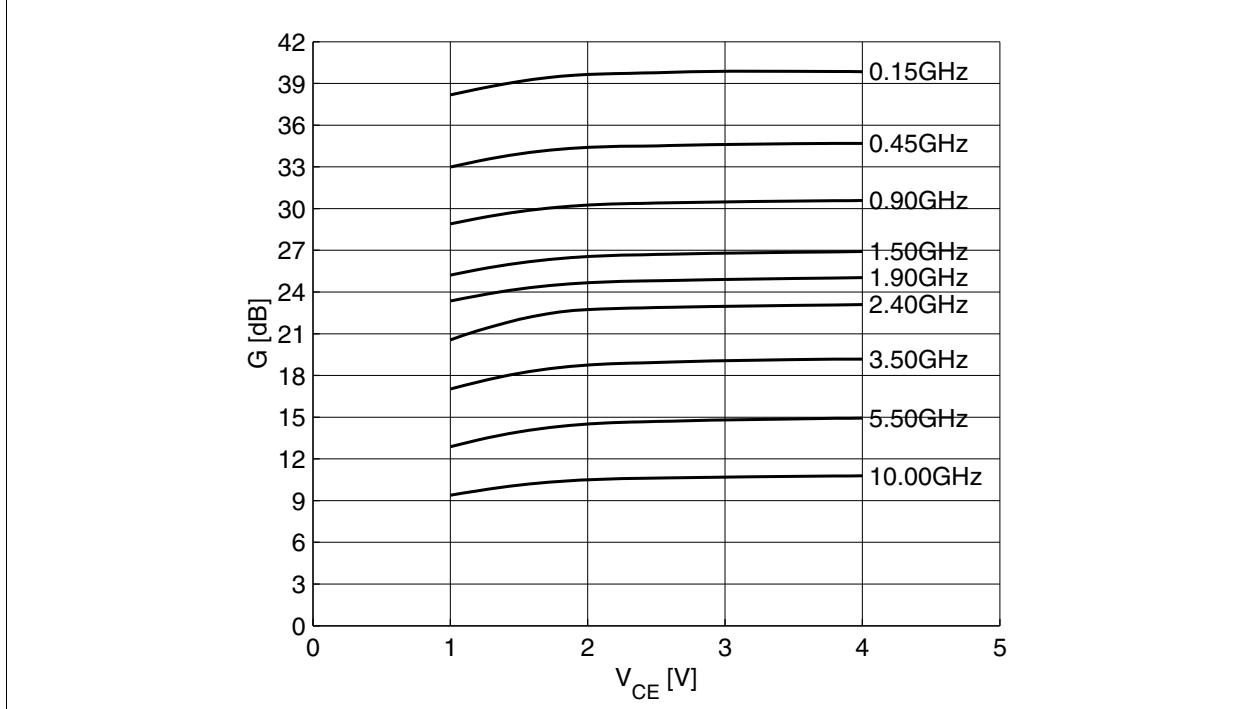
Figure 13   Maximum Power Gain $G_{max} = f(V_{CE})$, I_C = 30 mA, f = Parameter in GHz
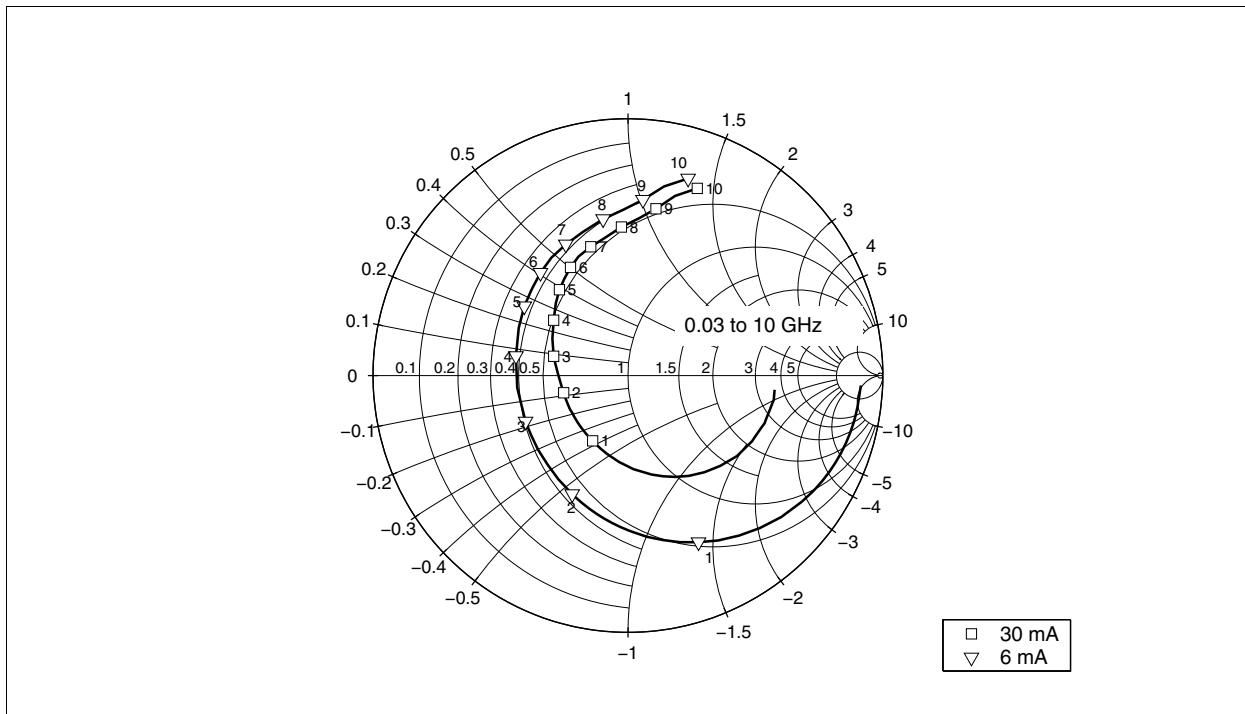
Figure 14   Input Matching $S_{11} = f(f)$, V_{CE} = 3 V, I_C = 6 / 30 mA
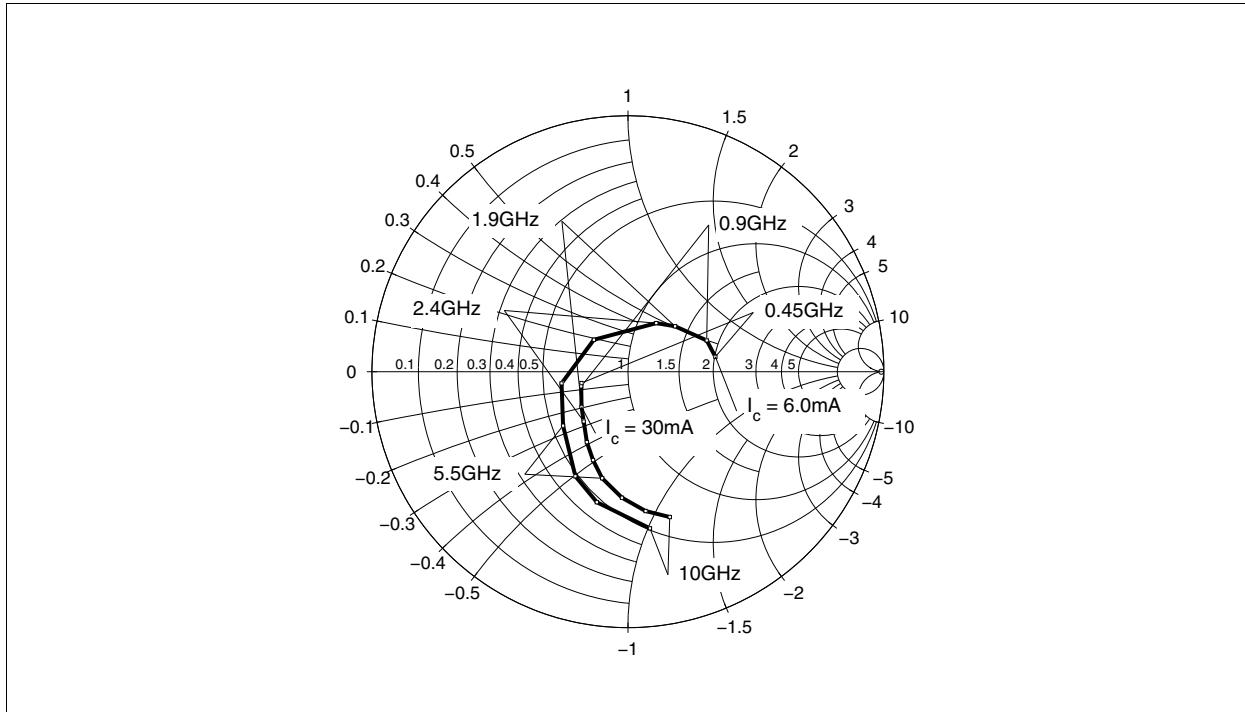
Figure 15   Source Impedance for Minimum Noise Figure $Z_{opt} = f(f)$, V_{CE} = 3 V, I_C = 6 / 30 mA
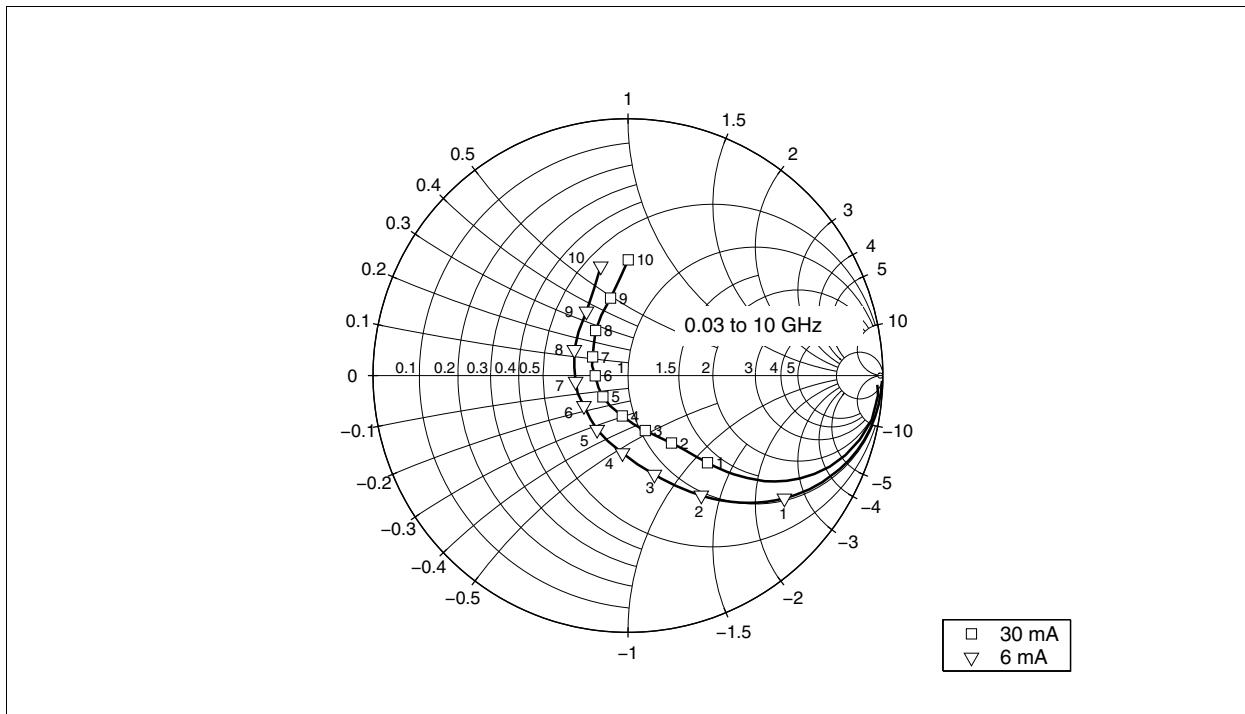
Figure 16   Output Matching $S_{22} = f(f)$, V_{CE} = 3 V, I_C = 6 / 30 mA
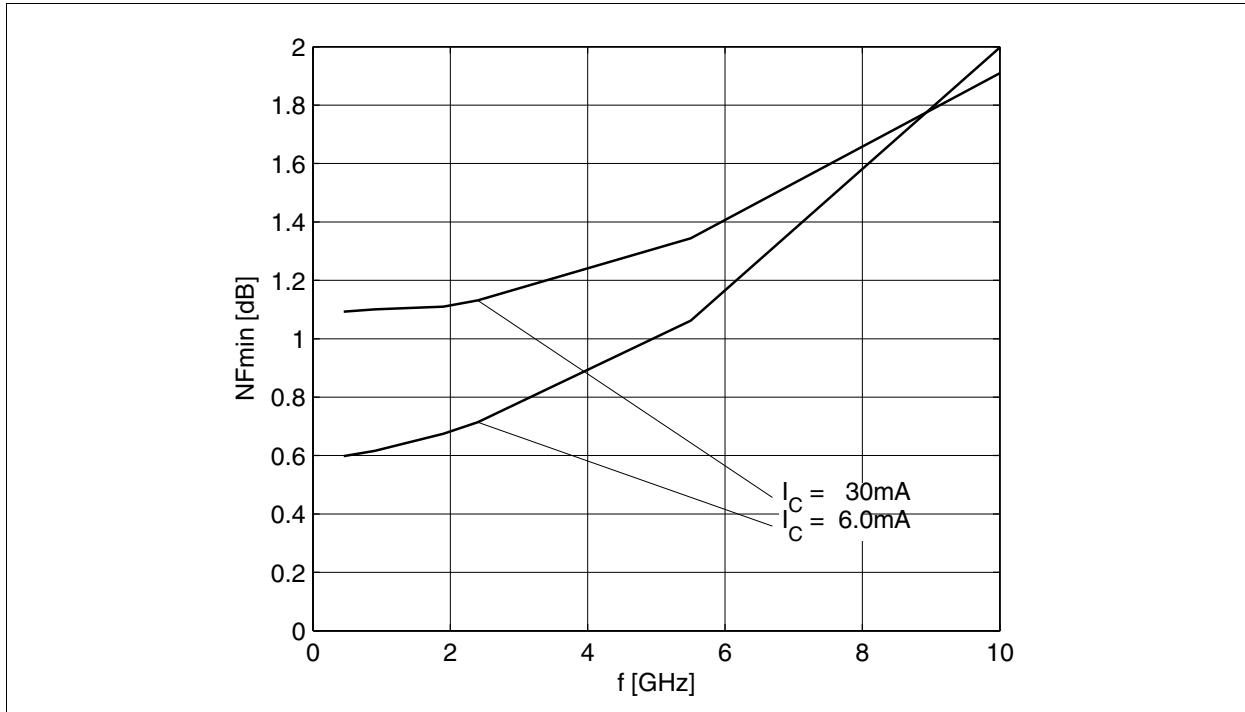
Figure 17   Noise Figure $NF_{min} = f(f)$, V_{CE} = 3 V, I_C = 6 / 30 mA, $Z_S = Z_{opt}$
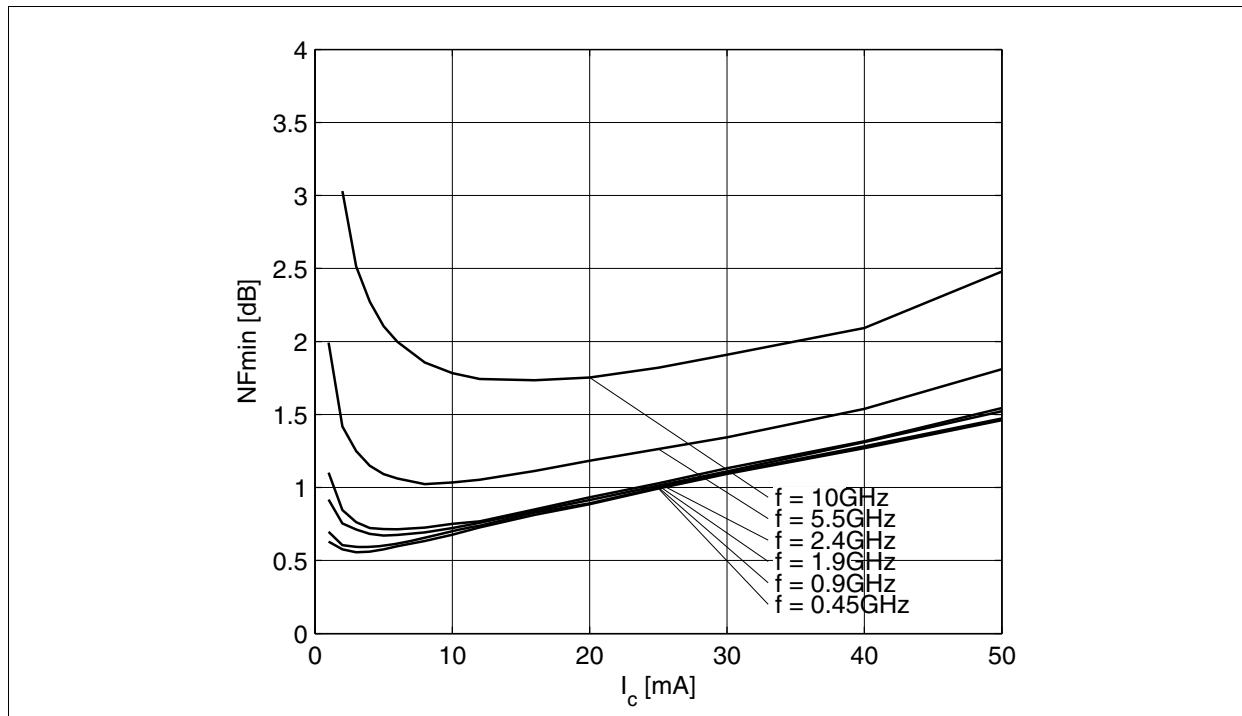
**Figure 18** Noise Figure $NF_{min} = f(I_C)$, $V_{CE} = 3$ V, $Z_S = Z_{opt}$, f = Parameter in GHz
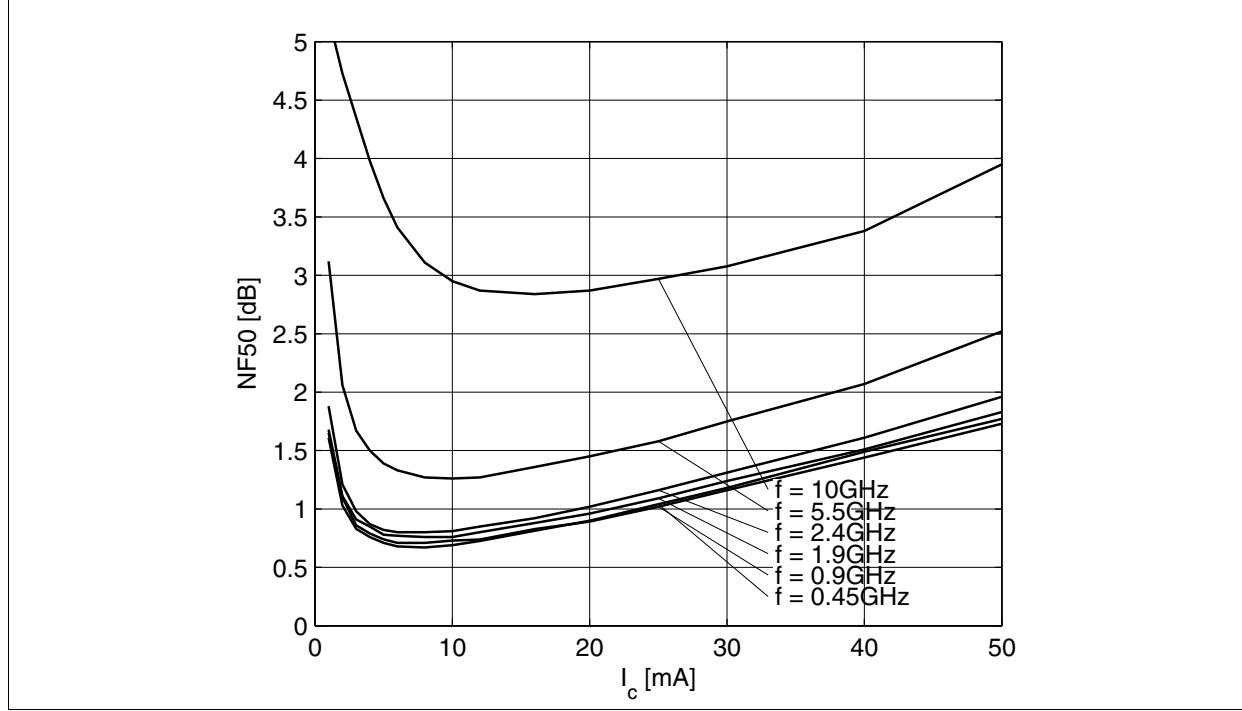
Figure 19 Noise Figure $NF_{50} = f(I_C)$, $V_{CE} = 3$ V, $Z_S = 50$ Ω, f = Parameter in GHz

Note: The curves shown in this chapter have been generated using typical devices but shall not be considered as a guarantee that all devices have identical characteristic curves. $T_A = 25°C$.

6 Simulation Data

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website: **www.infineon.com/rf.models**. Please consult our website and download the latest versions before actually starting your design.

You find the BFP640ESD SPICE GP model in the internet in MWO- and ADS-format, which you can import into these circuit simulation tools very quickly and conveniently. The model already contains the package parasitics and is ready to use for DC- and high frequency simulations. The terminals of the model circuit correspond to the pin configuration of the device.

The model parameters have been extracted and verified up to 10 GHz using typical devices. The BFP640ESD SPICE GP model reflects the typical DC- and RF-performance within the limitations which are given by the SPICE GP model itself. Besides the DC characteristics all S-parameters in magnitude and phase, as well as noise figure (including optimum source impedance, equivalent noise resistance and flicker noise) and intermodulation have been extracted.

7 Package Information SOT343
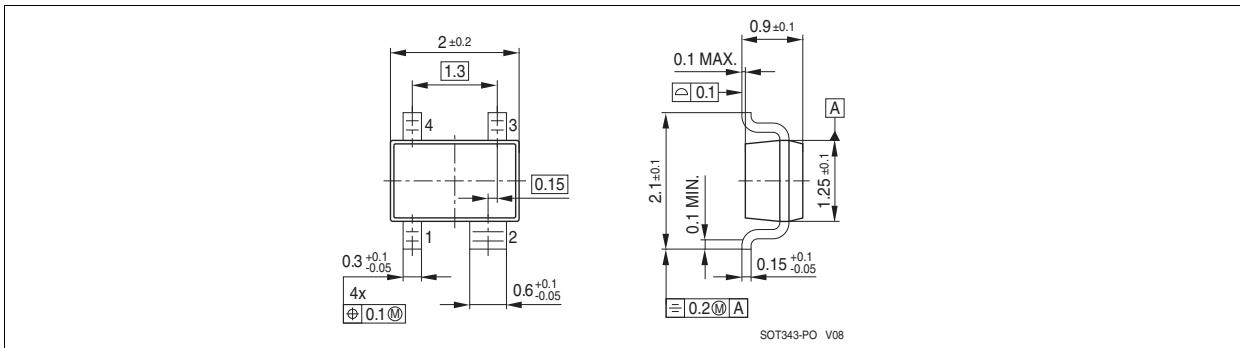

Figure 20   Package Outline
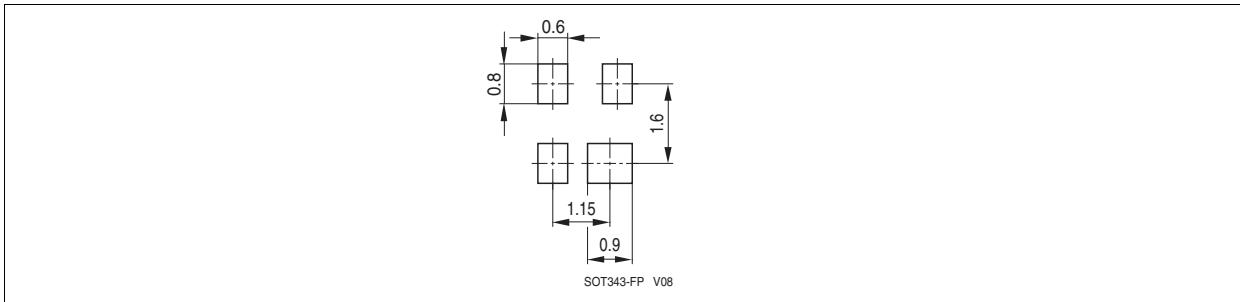
Figure 21   Package Foot Print
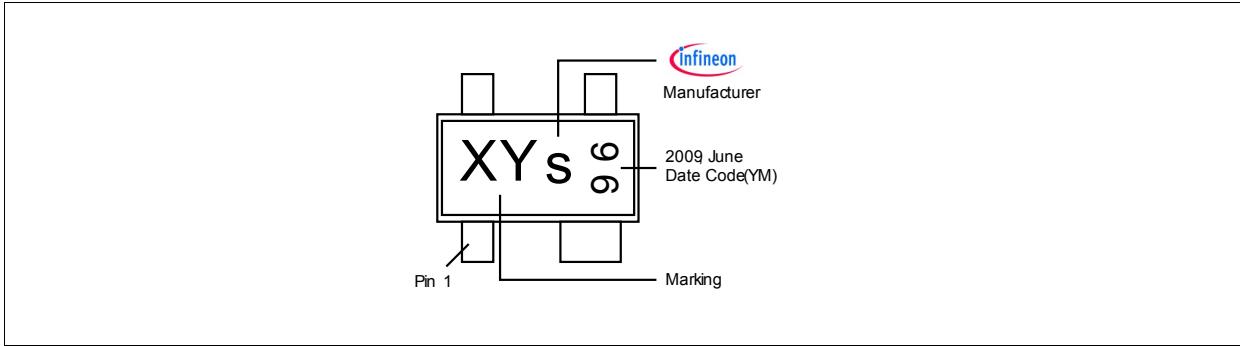
**Figure 22   Marking Description (Marking BFP640ESD: T4s)**
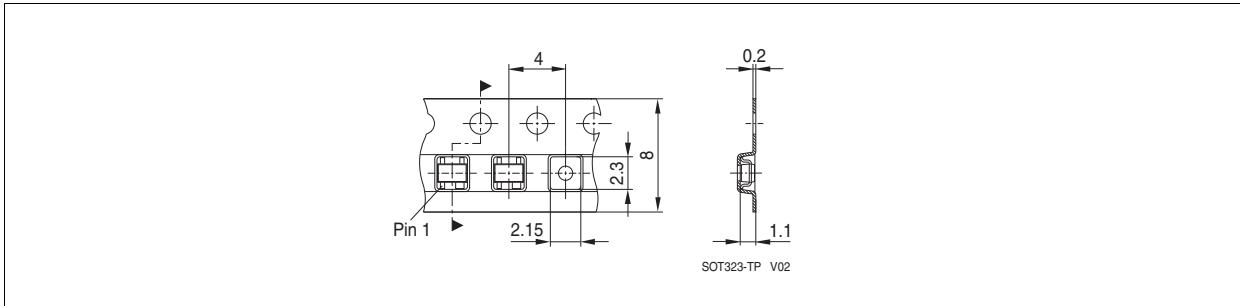

Figure 23   Tape Dimensions

www.infineon.com